

Precision Monolithics Inc.

FEATURES

•	Low Offset Voltage 150μV Max
	Low Offset Voltage Drift 2.5 µV/° C Max
	Five Times PM108A Output Current 5mA Min
	Low Offset Current 200pA Max
•	Low Bias Current
•	Low Power Consumption 18mW Max @ ±15V
•	High Common-Mode Input Range ±13.5V Min
•	MiL-STD-883 Class B Processing Available

- Silicon-Nitride Passivation
- 125° C Temperature-Tested Dice
- Available in Die Form

ORDERING INFORMATION †

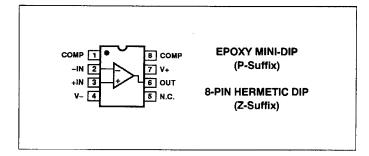
T _ 25°C	PACI	KAGE	ODEDATING		
T _A = 25°C V _{OS} MAX (mV)	CERDIP 8-PIN	PLASTIC 8-PIN	OPERATING TEMPERATURE RANGE		
0.15	OP08AZ	_	MIL		
0.15	_	OP08EP	COM		
1.0	OP08GZ	_	СОМ		

Burn-in is available on commercial and industrial temperature range parts in CerDIP and plastic DIP packages. For ordering information, see 1990/91 Data Book, Section 2.

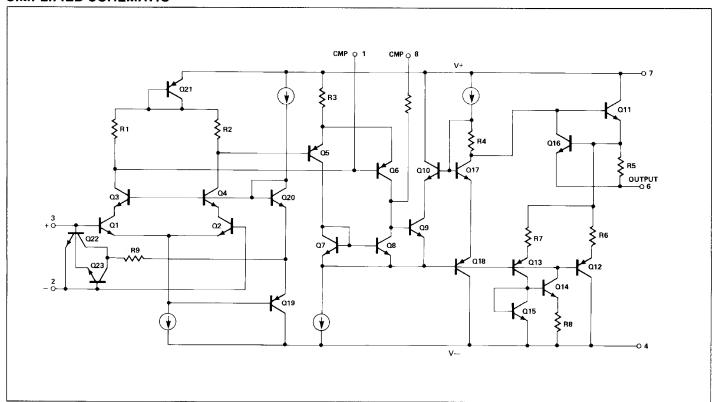
GENERAL DESCRIPTION

The PMI OP-08 is an improved version of the popular LM108A low-power op amp. Excellent performance is achieved by applying PMI's ion-implanted super-beta process and onchip-zener-zap trimming. The OP-08 has a three-times lower offset voltage and a two-times lower offset voltage drift. Worst-case input offset voltage over -55° C to +125° C for the OP-08 is only $350\mu V$. In addition, the OP-08 has five times the output current capability of the 108A. For an op amp with identical specifications plus internal frequency compensation, see the OP-12 data sheet.

PIN CONNECTIONS



SIMPLIFIED SCHEMATIC





ABSOLUTE MAXIMUM RATINGS (Note	4)
Supply Voltage	•
OP-08A, OP-08E (All DICE Except GR)	±20V
OP-08G (GR DICE Only)	±18V
Differential Input Current (Note 1)	±10mA
Input Voltage (Note 2)	±15V
Output Short-Circuit Duration	Indefinite
Operating Temperature Range	
OP-08A	
OP-08E, OP-08G	0°C to +70°C
Storage Temperature Range (Z)	65°C to +150°C
Storage Temperature Range (P)	65°C to +125°C
Lead Temperature (Soldering, 60 sec)	300°C
DICE Junction Temperature (T _j)	65°C to +150°C

PACKAGE TYPE	Θ _{JA} (Note 3)	elc	UNITS
8-Pin Hermetic DIP (Z)	162	26	°C/W
8-Pin Plastic DIP (P)	110	50	°C/W

NOTES:

- The inputs are shunted with back-to-back diodes for overvoltage protection.
 Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs without some limiting resistance.
- 2. For supply voltages less than $\pm 15 \text{V}$, the absolute maximum input voltage is equal to the supply voltage.
- Θ_{jA} is specified for worst case mounting conditions, i.e., Θ_{jA} is specified for device in socket for CerDIP and P-DIP packages.
- Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

ELECTRICAL CHARACTERISTICS at $T_A = \pm 25$ °C, $V_S = \pm 20$ V for A and E Grades, $V_S = \pm 15$ V for G Grade, unless otherwise noted. Compensation capacitor = 30pF.

			(OP-08A/E			OP-08G			
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS	
Input Offset Voltage	Vos		_	0.07	0.15	_	0.25	1.0	m۷	
Input Offset Current	Ios		_	0.05	0.20	_	0.08	0.50	n.A	
Input Bias Current	IB		_	0.80	2.0		1.0	5.0	n.A	
Input Noise Voltage	e _{np-p}	0.1Hz to 10Hz	_	0.9	_	_	0.9	_	µ۷ _{p-p}	
Input Noise Voitage Density	e _n	$f_{O} = 10Hz$ $f_{O} = 100Hz$ $f_{O} = 1000Hz$	_ _ _	22 21 20	<u>-</u>		22 21 20	_ _ _	nV/√Hz	
Input Noise Current	i _{np-p}	0.1Hz to 10Hz	_	3		_	3		pA _{p-p}	
Input Noise Current Density	in	$f_{O} = 10Hz$ $f_{O} = 100Hz$ $f_{O} = 1000Hz$	_ _ _	0.15 0.14 0.13	- -	_ _ _	0.15 0.14 0.13	<u>-</u> -	p A /√Hz	
Input Resistance — Differential Mode	R _{IN}	(Note 1)	26	70	_	10	50	_	MΩ	
Input Voltage Range	IVR	$V_S = \pm 15V$	± 13.5	± 14.0	_	± 13.5	± 14.0		V	
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 13.5V$	104	120	_	84	116	_	dB	
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 15V$	_	1	7	· –	2	63	μV/V	
Large-Signal Voltage Gain	Avo	$R_{L} \ge 10k\Omega,$ $V_{O} = \pm 10V$ $R_{L} \ge 2k\Omega,$ $V_{O} = \pm 10V,$ $V_{S} = \pm 15V$	80 50	300 150	_	40	250 100	-	V/mV	
Output Voltage Swing	Vo	$R_{L} \ge 10k\Omega,$ $V_{S} = \pm 15V$ $R_{L} \ge 2k\Omega,$ $V_{S} = \pm 16V$	±13 ±10	±14 ±12	_	±13 ±10	±14 ±12	_ _	V	
Slew Rate	SR	$H_L \ge 2k\Omega$	_	0.12	_	_	0.12	_	V/μs	
Closed-Loop Bandwidth	BW	A _{VCL} = +1	_	0.8	_	_	8.0	_	MHz	
Open-Loop Output Resistance	Ro	$\mathbf{v_O} = \mathbf{v}, \ \mathbf{I_O} = \mathbf{v}$		200	_	_	200	_	11	
Power Consumption	P _d	V _S = ± 15V V _S = ±5V		9	18 6		12 4	24 8	mW	

NOTE:

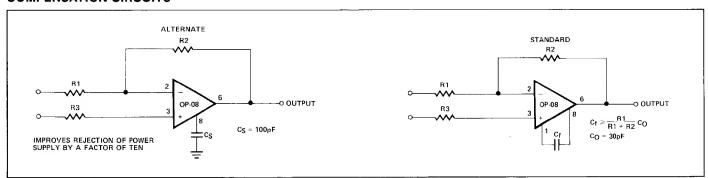
1. Guaranteed by input bias current.



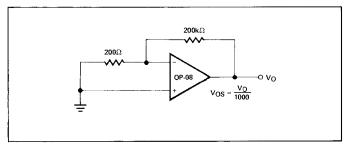
ELECTRICAL CHARACTERISTICS $V_S = \pm 20V$ for A Grade, $-55^{\circ}C \le T_A \le +125^{\circ}C$, unless otherwise noted.

				OP-08A		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage	V _{os}		-	0.12	0.35	mV
Average Input Offset Voltage Drift	TCV _{os}		_	0.50	2.5	μV/°C
Input Offset Current	los			0.12	0.40	nA
Average Input Offset Current Drift	TCI _{OS}		_	0.50	2.5	pA/°C
Input Bias Current	I _B		_	1.2	3.0	nA
Input Voltage Range	IVR	V _S = ±15V	±13.5	±14.0	_	V
Common-Mode Rejection Ratio	CMRR	V _{CM} = ±13.5	100	110	-	₫B
Power Supply Rejection Ratio	PSRR	V _S = ±5V to ±15V	_	4	10	μ٧/٧
Large-Signal Voltage Gain	A _{VO}	$R_L \ge 5k\Omega$, $V_O = \pm 10V$, $V_S = \pm 15V$	40	120	-	V/mV
Output Voltage Swing	v _o	$R_L \ge 10k\Omega$, $V_S = \pm 15V$ $R_L \ge 5k\Omega$, $V_S = \pm 15V$	±13 ±10	±14 ±12	<u>-</u>	V
Power Consumption	P _d	V _S = ±15V	_	9	18	mW

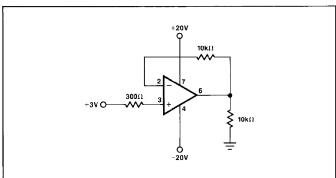
COMPENSATION CIRCUITS



OFFSET VOLTAGE TEST CIRCUIT



BURN-IN CIRCUIT



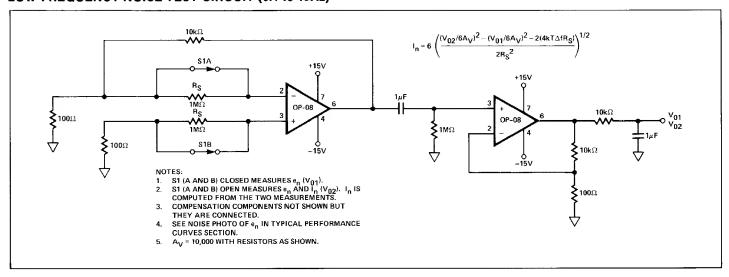


ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$ for G Grade and $V_S = \pm 20V$ for E Grade, $0^{\circ}C \le T_A \le +70^{\circ}C$, unless otherwise noted.

			OP-08E				3		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Input Offset Voltage	Vos	*		0.10	0.26		0.32	1.4	mV
Average Input Offset Voltage Drift	TCV _{OS}	(Note 1)	<u> </u>	0.50	2.5	_	1.5	10	μV/° C
Input Offset Current	I _{OS}		_	80.0	0.30	_	0.12	6.5	nA
Average Input Offset Current Drift	TCI _{OS}	(Note 1)	_	0.50	2.5	_	2.0	50	pA/°C
Input Bias Current	I _B		<u> </u>	1.0	2.6	_	1.4	6.5	nA
Input Voltage Range	IVR	$V_S = \pm 15V$	±13.5	±14.0	_	± 13.5	±14.0	_	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 13.5V$	100	116	_	80	112	_	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 15V$		2	10	_	3	100	μV/V
Large-Signal Voltage Gain	A _{VO}	$\begin{aligned} R_L &\geq 2k\Omega, \\ V_O &= \pm 10V \\ R_L &\geq 10k\Omega, \\ V_O &= \pm 10V \\ V_S &= \pm 15V \end{aligned}$	25 60	100 200	<u>-</u>	_ 25	80 150	-	V/mV
Output Voltage	Vo	$R_L \ge 10k\Omega$, $V_S = \pm 15V$	±13	± 14	_	±13	±14	_	v
Swing	Ü	$R_L \ge 2k\Omega$, $V_S = \pm 15V$	±10	±12		± 10	±12	_	
Power Consumption	P _d	V _S = ±15V	_	9	18		15	24	mW

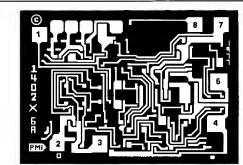
NOTE:

LOW-FREQUENCY NOISE TEST CIRCUIT (0.1 to 10Hz)



^{1.} Sample tested.

DICE CHARACTERISTICS (125°C TESTED DICE AVAILABLE)



DIE SIZE 0.059×0.043 inch, 2537 sq. mils (1.50 \times 1.09 mm, 1.64 sq. mm)

- 1. COMPENSATION
- 2. INVERTING INPUT
- 3. NONINVERTING INPUT
- 4. V-
- 6. OUTPUT
- 7. V+
- 8. COMPENSATION

For additional DICE ordering information, refer to 1990/91 Data Book, Section 2.

WAFER TEST LIMITS at $V_S = \pm 20V$ and $T_A = 25^{\circ}$ C for OP-08N and OP-08G devices; $V_S = \pm 20V$ and $T_A = 125^{\circ}$ C for OP-08NT and OP-08GT devices; $V_S = \pm 15V$ and $T_A = 25^{\circ}$ C for OP-08GR devices, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-08NT	OP-08N	OP-08GT	OP-08G LIMIT	OP-08GR LIMIT	UNITS
Input Offset Voltage	Vos		0.35	0.15	0.6	0.3	1.0	mV MAX
Input Offset Current	los		0.4	0.2	0.4	0.2	0.5	nA MAX
Input Bias Current	I _B		3	2	4	2	5	nA MAX
Input Voltage Range	IVR	V _S = ±15V	± 13.5	± 13.5	± 13.5	± 13.5	± 13.5	V MIN
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 13V$ $V_{S} = \pm 15V$	100	104	100	104	84	dB MIN
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 15V$	10	7	10	7	63	μV/V MAX
Output Voltage Swing	V _O	$\begin{split} V_S &= \pm 15 V \\ R_L &\geq 10 k \Omega \\ R_L &\geq 2 k \Omega \\ R_L &\geq 5 k \Omega \end{split}$	±13 — ±10	±13 ±10	± 13 — ± 10	±13 ±10 —	± 13 ± 10 —	V MIN
Large-Signal Voltage Gain $(V_0 = \pm 10V)$	A _{VO}	$\begin{aligned} R_L &\geq 10 k \Omega \\ R_L &\geq 2 k \Omega, \ V_S = \pm 15 V \\ R_L &\geq 5 k \Omega, \ V_S = \pm 15 V \end{aligned}$	- - 40	80 50 —		80 50 —	40 _ _	V/mV MIN
Input Resistance	R _{IN}	(Note 2)	_	25		25	10	ΜΩ ΜΙΝ
Supply Current	I _{SY}	$I_{OUT} = 0, V_{S} = \pm 15V$ $V_{OUT} = 0$	0.6	0.6	0.6	0.6	0.8	mA MAX

NOTES:

Electrical tests are performed at wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on dice lot qualification through sample lot assembly and testing.

TYPICAL ELECTRICAL CHARACTERISTICS at $V_S = \pm 15 V$, unless otherwise noted.

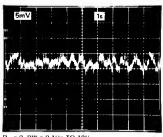
PARAMETER	SYMBOL CONDITIONS	OP-08NT TYPICAL	OP-08N TYPICAL	OP-08GT TYPICAL	OP-08G TYPICAL	OP-08GR TYPICAL	UNITS
Average Input Offset Voltage Drift	TCV _{OS}	0.5	0.5	1.0	1.0	1.5	μV/° C
Average Input Offset Current Drift	TCI _{OS}	0.5	0.5	0.5	0.5	1.0	pA/°C

For 25°C characteristics of NT & GT devices, see N & G characteristics, respectively.

^{2.} Guaranteed by input bias current.

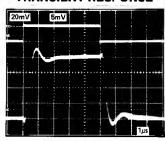
TYPICAL PERFORMANCE CHARACTERISTICS

LOW FREQUENCY NOISE

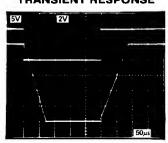


R_S = 0, BW = 0.1Hz TO 10Hz 5mV/DIV AT READOUT 0.5µV/DIV REFERRED TO INPUT

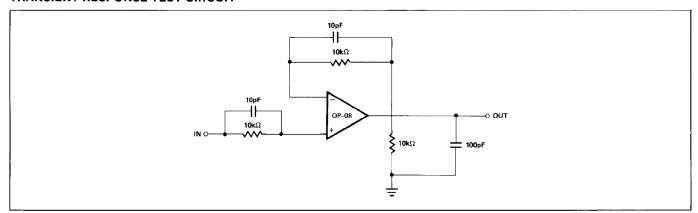
SMALL-SIGNAL TRANSIENT RESPONSE



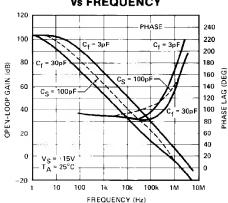
LARGE-SIGNAL TRANSIENT RESPONSE



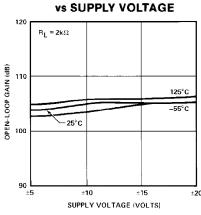
TRANSIENT RESPONSE TEST CIRCUIT



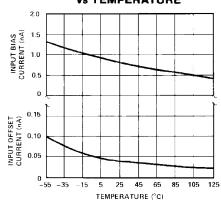
OPEN-LOOP GAIN AND PHASE vs FREQUENCY



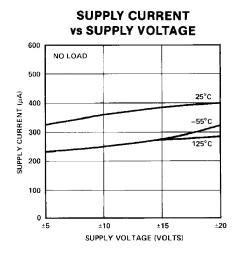
OPEN-LOOP GAIN vs SUPPLY VOLTAGE

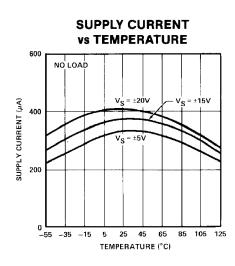


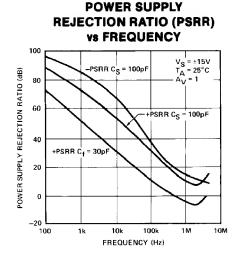
INPUT BIAS CURRENT
AND INPUT OFFSET CURRENT
vs TEMPERATURE



TYPICAL PERFORMANCE CHARACTERISTICS





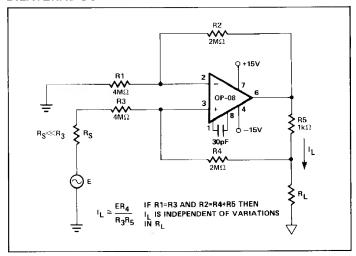


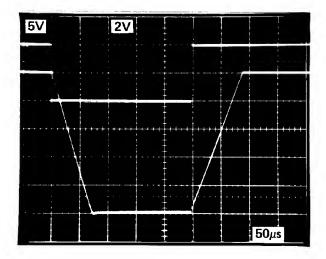
APPLICATIONS INFORMATION

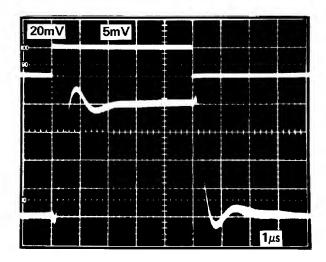
The OP-08 series has very low input offset and bias currents; the user is cautioned that printed circuit board leakage currents can produce significant errors, especially at high board temperatures. Careful attention to board layout and cleaning procedure is needed to take full advantage of the OP-08 performance. Board leakage is minimized by encircling the input pins with a guard ring maintained at the same potential as the inputs. This guard ring should be driven by a low impedance source, such as an amplifier's output or ground.

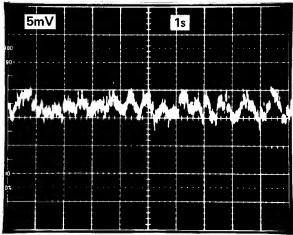
TYPICAL APPLICATION

BILATERAL CURRENT SOURCE

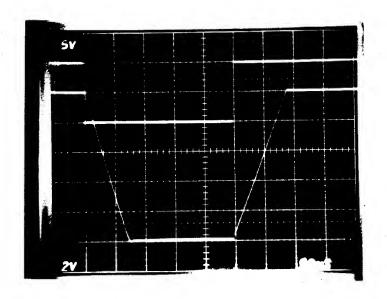






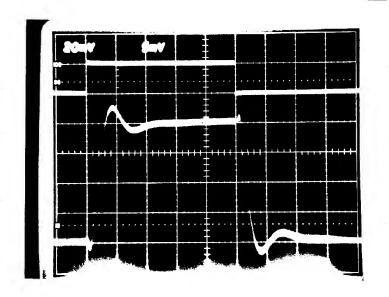


 R_S = 0, BW = 0.1Hz TO 10Hz 5mV/DIV AT READOUT 0.5 μ V/DIV REFERRED TO INPUT



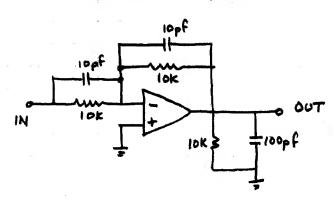
0P08, 12

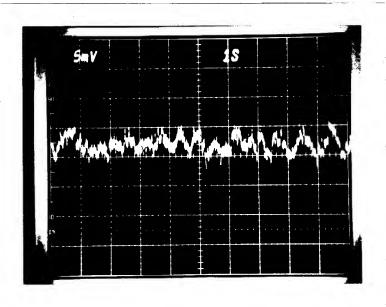
LARGE SIGNAL RESP.



OP 08 , 12

TRANSIENT RESP





OP 08, 12

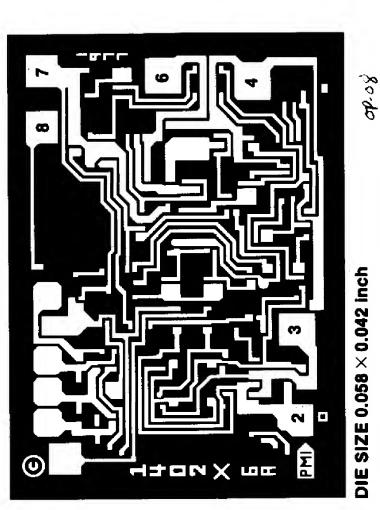
LOW FREQ NOISE

Rs = 0 , 8 W = 0. 1 Hz to 10 Hz

SmV/dry AT OUTPUT

5 NV REFERRED TO INPUT

09-08



DIE SIZE 0.058 imes 0.042 inch

1. COMPENSATION
2. INVERTING INPUT
3. NON-INVERTING INPUT

6. OUTPUT
7. V+
8. COMPENSATION